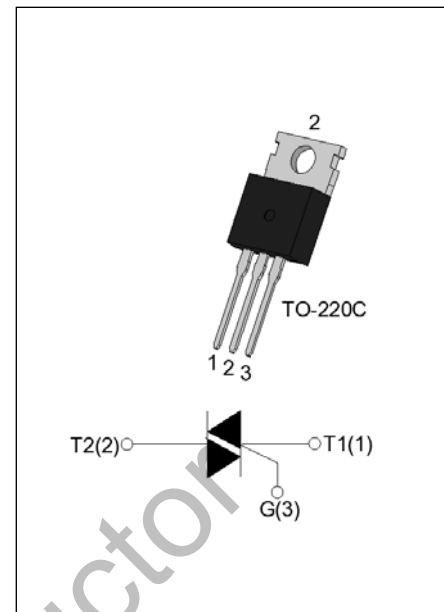


DESCRIPTION:

The BT136-800E triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. From T2 terminals to external heatsink. Package TO-220C is RoHS compliant.

MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	4	A
V_{DRM}/V_{RRM}	800	V
$I_{GT\ I/II/III/IV}$	10/10/10/25	mA



ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Value	Unit
Storage junction temperature range		T_{stg}	-40-150	$^{\circ}C$
Operating junction temperature range		T_j	-40-125	$^{\circ}C$
Repetitive peak off-state voltage ($T_j=25^{\circ}C$)		V_{DRM}	800	V
Repetitive peak reverse voltage ($T_j=25^{\circ}C$)		V_{RRM}	800	V
RMS on-state current ($T_C \leq 110^{\circ}C$)		$I_{T(RMS)}$	4	A
Non repetitive surge peak on-state current (full cycle , $t_p=20ms$, $T_j=25^{\circ}C$)		I_{TSM}	35	A
Non repetitive surge peak on-state current (full cycle , $t_p=16.6ms$, $T_j=25^{\circ}C$)			38.5	
I^2t value for fusing ($t_p=10ms$, $T_j=25^{\circ}C$)		I^2t	6.1	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$, $f=100Hz$, $T_j=125^{\circ}C$)	I - II -III	di/dt	80	$A/\mu s$
	IV		40	
Peak gate current ($t_p=20\mu s$, $T_j=125^{\circ}C$)		I_{GM}	2	A
Average gate power dissipation ($T_j=125^{\circ}C$)		$P_{G(AV)}$	0.5	W
Peak gate power		P_{GM}	5	W
Peak pulse voltage ($T_j=25^{\circ}C$; non-repetitive,off-state;FIG.7)		V_{pp}	3.5	kV

ELECTRICAL CHARACTERISTICS (T_j=25°C unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I _{GT}	V _D =12V R _L =33Ω	I - II - III	MAX.	10	mA
		IV		25	
V _{GT}		ALL	MAX.	1	V
V _{GD}	V _D =V _{DRM} T _j =125°C R _L =3.3KΩ	ALL	MIN.	0.2	V
I _L	I _G =1.2I _{GT}	I - III	MAX.	20	mA
		II - IV		30	
I _H	I _T =100mA		MAX.	25	mA
dV/dt	V _D =540V Gate Open T _j =110°C		MIN.	250	V/μs
(dV/dt) _c	(dI/dt) _c =1.8A/ms, T _j =110°C		MIN.	6	V/μs
t _{on}	I _G =40mA I _A =200mA I _R =20mA		TYP.	1.5	μs
t _{off}	T _j =25°C			15	

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V _{TM}	I _{TM} =5A t _p =380μs	T _j =25°C	1.7	V
V _{TO}	Threshold voltage	T _j =125°C	0.94	V
R _D	Dynamic resistance	T _j =125°C	124	mΩ
I _{DRM}	V _D =V _{DRM} V _R =V _{RDM}	T _j =25°C	5	μA
I _{RDM}		T _j =125°C	0.4	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
R _{th(j-c)}	junction to case (AC)	2.3	°C/W
R _{th(j-a)}	junction to ambient (AC)	60	°C/W

FIG.1 Maximum power dissipation versus RMS on-state current

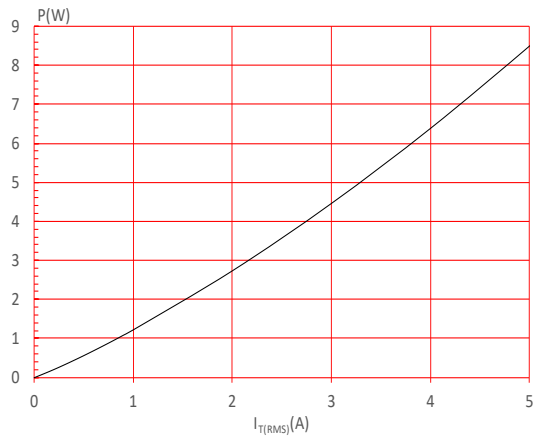


FIG.2: RMS on-state current versus case temperature

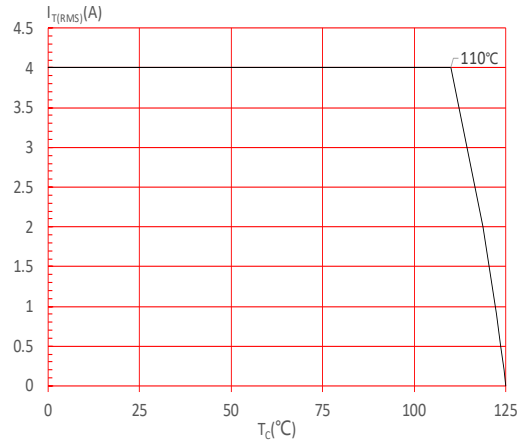


FIG.3: Surge peak on-state current versus number of cycles

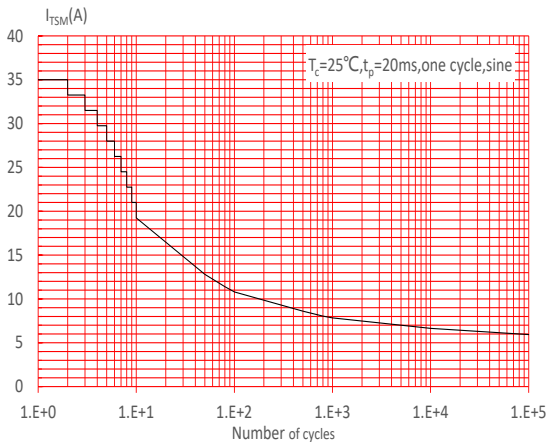


FIG.4: On-state characteristics

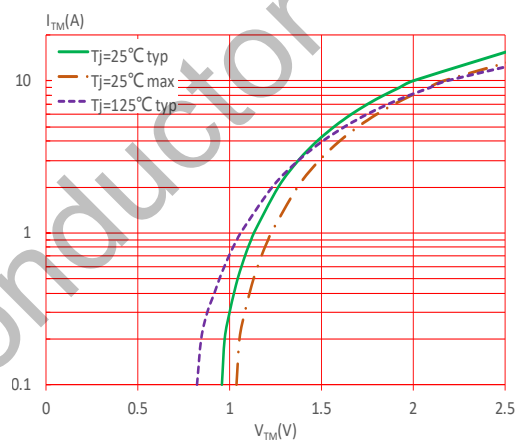


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$, and corresponding value of I^2t (I - II -III: $di/dt < 80\text{A}/\mu\text{s}$; IV: $di/dt < 40\text{A}/\mu\text{s}$)

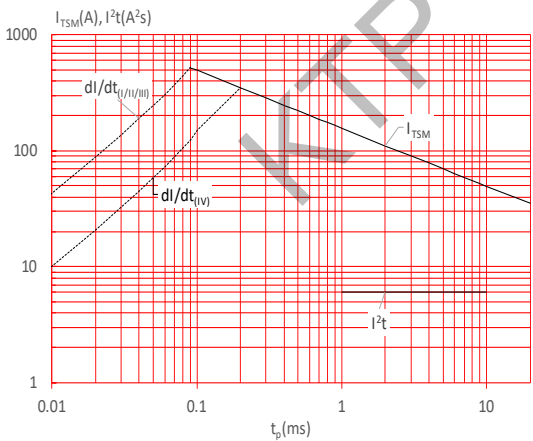


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature

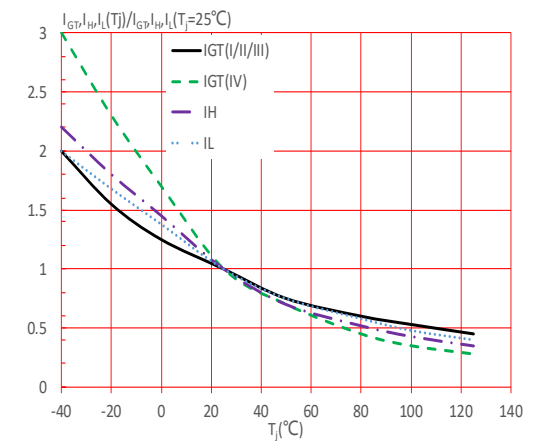
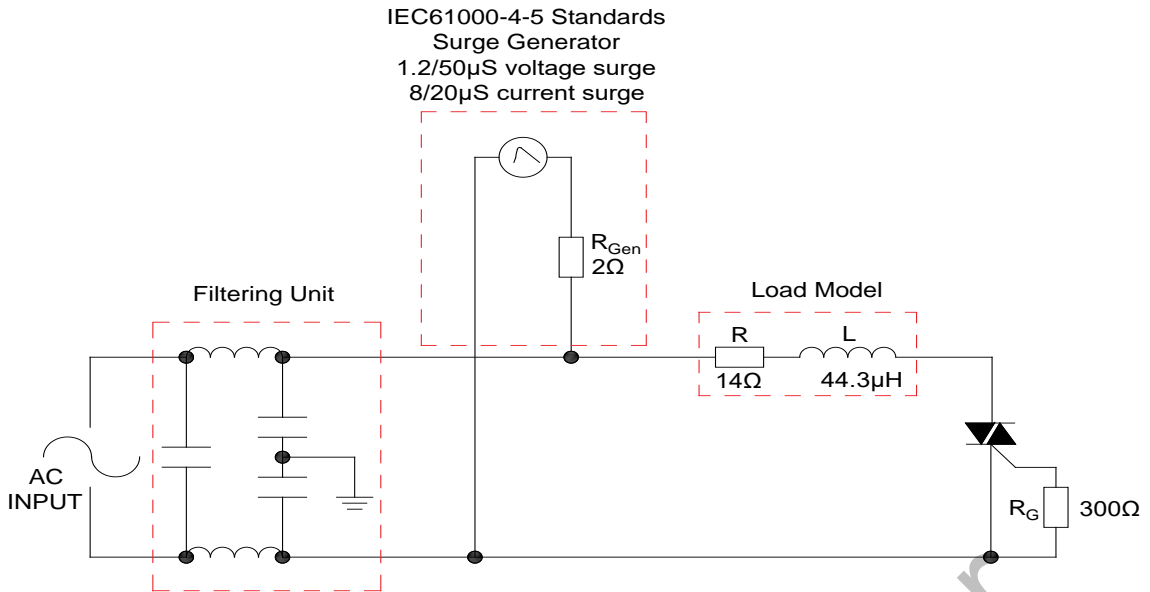
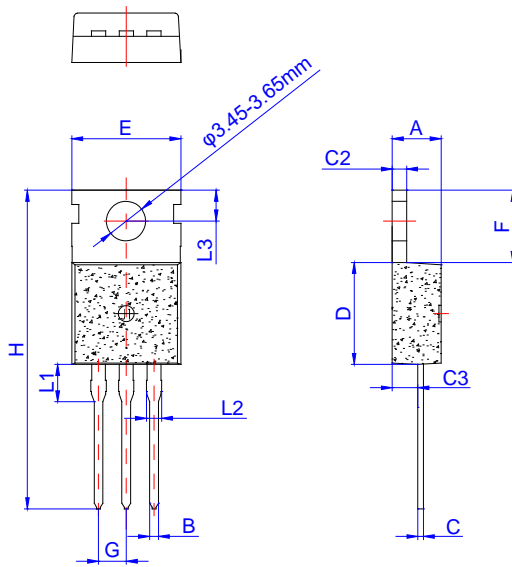


FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



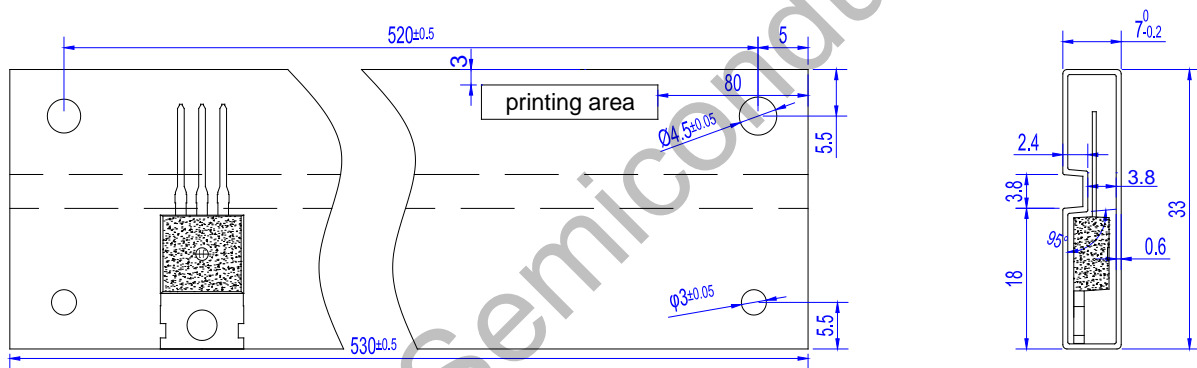
KTP Semiconductor

PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.70		0.90	0.028		0.035
C	0.45		0.60	0.018		0.024
C2	1.25		1.35	0.049		0.053
C3	2.20		2.60	0.087		0.102
D	8.90		9.90	0.350		0.390
E	9.90		10.3	0.390		0.406
F	6.30		6.90	0.248		0.272
G	2.40		2.70	0.094		0.106
H	28.0		29.8	1.102		1.173
L1	2.70		3.30	0.106		0.130
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116

DELIVERY MODE



PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
TO-220C	TUBE	50	1,000	5,000